Product Summary

Device	BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
Q1	20V	0.4Ω @ V_{GS} = 4.5V	1.34A
		0.5Ω @ V_{GS} = 2.5V	1.65A
Q2	-20V	0.7Ω @ V_{GS} = -4.5V	-1.14A
		0.9Ω @ V_{GS} = -2.5V	-0.94A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage $V_{GS(TH)}$ < 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **ESD Protected Gate to 2.5kV HBM**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMC2700UDMQ)**

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

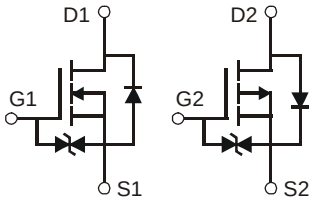
- Portable Electronics

Mechanical Data

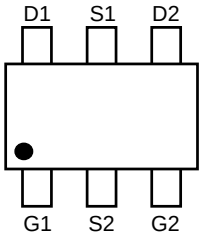
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.015 grams (Approximate)

SOT26

Top View



Device Symbol



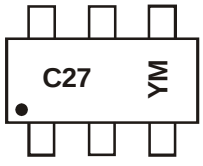
Top View
Pin-Out

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DMC2700UDM-7	C27	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



C27 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: F = 2018)
M = Month (ex: 9 = September)

Date Code Key

Year	2009	~	2018	2019	2020	2021	2022	2023	2024	2025
Code	W	~	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±6	V
Drain Current (Note 5)	T_A = +25°C T_A = +85°C	I_D	1.34 0.97	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	5	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	5	A

Maximum Ratings P-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±6	V
Drain Current (Note 5)	T_A = +25°C T_A = +85°C	I_D	-1.14 -1.07	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	-2.5	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	-2.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	1.12	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	111	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Note: 5. For a device mounted on 25mm x 25mm FR-4 PCB board with a high coverage of single sided 1oz copper, in still air conditions with two active die.

Electrical Characteristics N-CHANNEL – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	100	nA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1.0	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— — —	0.3 0.4 0.5	0.4 0.5 0.7	Ω	V_{GS} = 4.5V, I_D = 600mA V_{GS} = 2.5V, I_D = 500mA V_{GS} = 1.8V, I_D = 350mA
Forward Transfer Admittance	$\|Y_{fs}\|$	—	1.4	—	S	V_{DS} = 10V, I_D = 400mA
Diode Forward Voltage (Note 6)	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 150mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	60.67	—	pF	V_{DS} = 16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	9.68	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	5.37	—	pF	
Total Gate Charge	Q_g	—	736.6	—	pC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	93.6	—		
Gate-Drain Charge	Q_{gd}	—	116.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.1	—	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47Ω, R_G = 10Ω, I_D = 200mA
Turn-On Rise Time	t_R	—	7.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	26.7	—		
Turn-Off Fall Time	t_F	—	12.3	—		

Electrical Characteristics P-CHANNEL – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-100	nA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±1.0	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.5 0.7 1.0	0.7 0.9 1.3	Ω	V_{GS} = -4.5V, I_D = -430mA V_{GS} = -2.5V, I_D = -300mA V_{GS} = -1.8V, I_D = -150mA
Forward Transfer Admittance	$\|Y_{fs}\|$	—	-0.9	—	S	V_{DS} = -10V, I_D = -250mA
Diode Forward Voltage (Note 6)	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -150mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	59.76	—	pF	V_{DS} = -16V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	12.07	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	6.36	—	pF	
Total Gate Charge	Q_g	—	622.4	—	pC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -250mA
Gate-Source Charge	Q_{gs}	—	100.3	—		
Gate-Drain Charge	Q_{gd}	—	132.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.1	—	ns	V_{DD} = -10V, V_{GS} = -4.5V, R_L = 47Ω, R_G = 10Ω, I_D = -200mA
Turn-On Rise Time	t_R	—	8.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	28.4	—		
Turn-Off Fall Time	t_F	—	20.7	—		

Note: 6. Short duration pulse test used to minimize self-heating effect.

N-CHANNEL – Q1

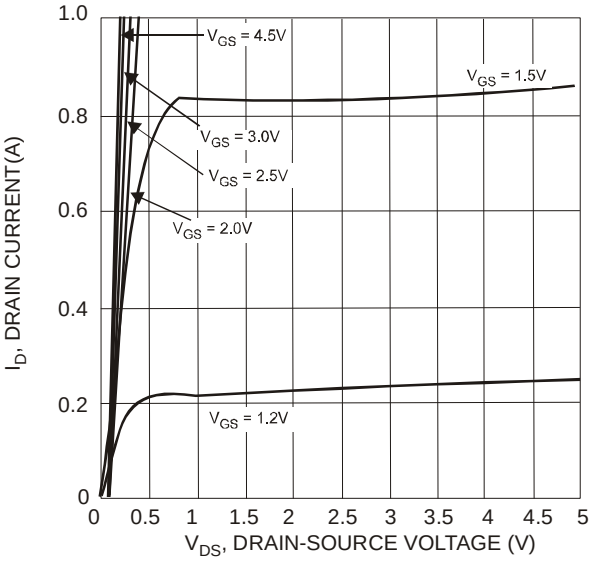


Fig.1 Typical Output Characteristics

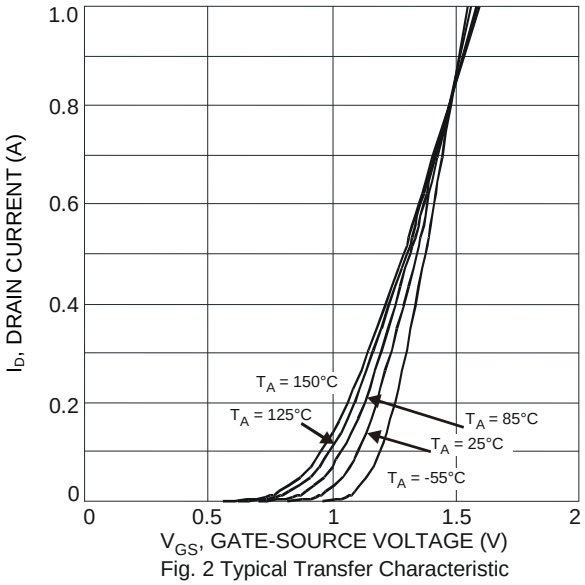


Fig. 2 Typical Transfer Characteristic

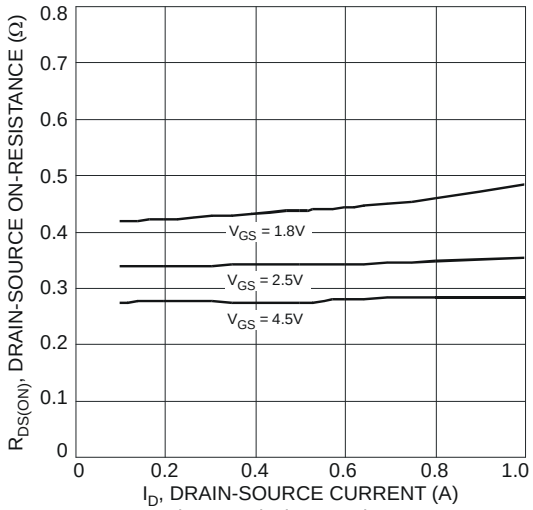


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

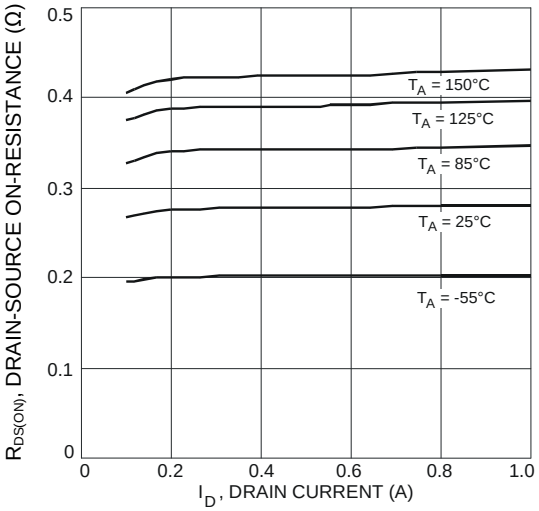


Fig. 4 Typical On-Resistance
vs. Drain Current and Temperature

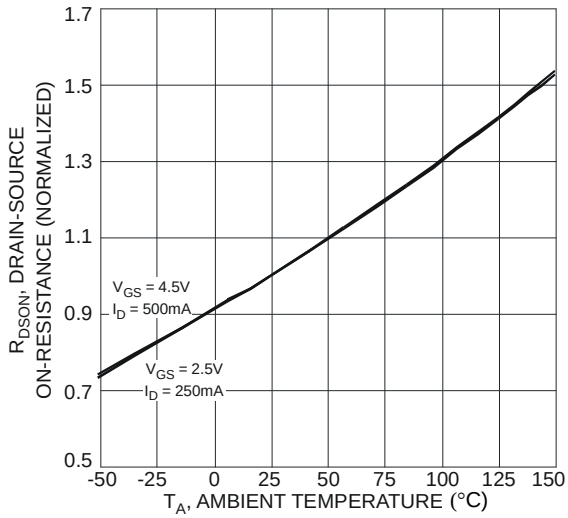


Fig. 5 On-Resistance Variation with Temperature

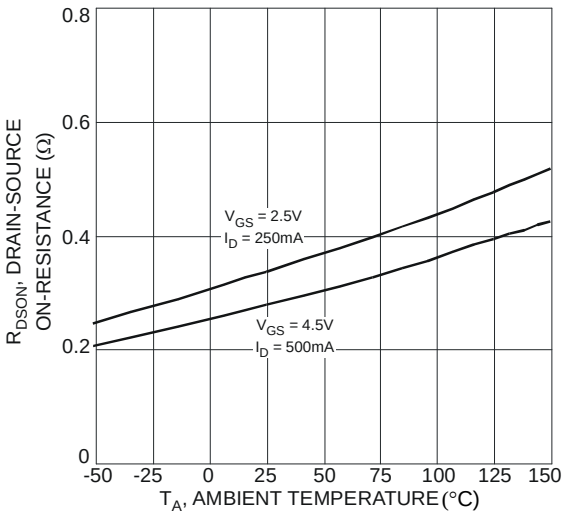


Fig. 6 On-Resistance Variation with Temperature

N-CHANNEL – Q1 (Cont.)

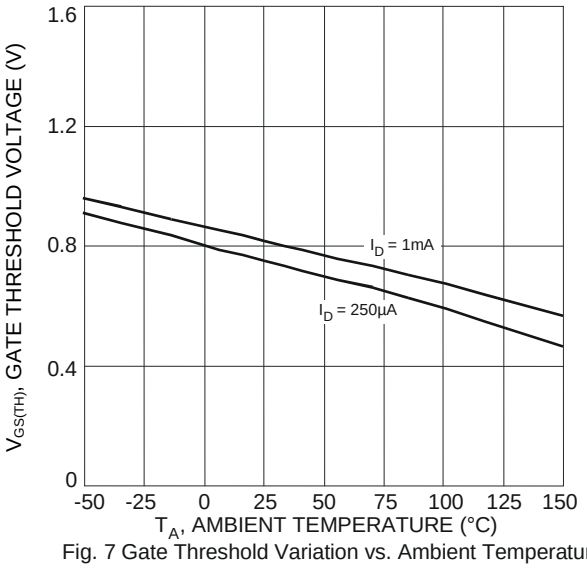


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

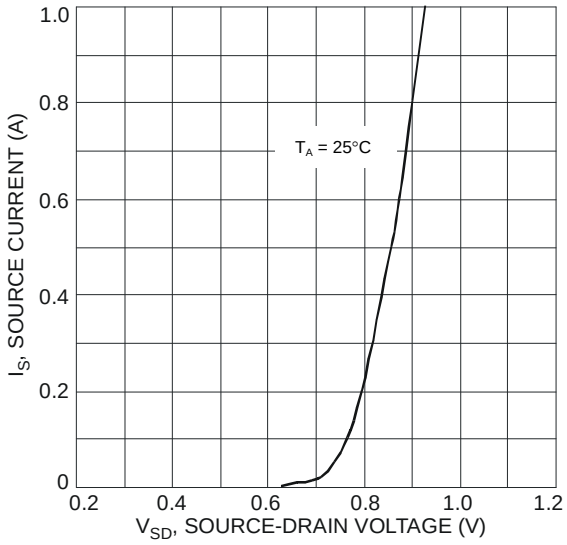


Fig. 8 Diode Forward Voltage vs. Current

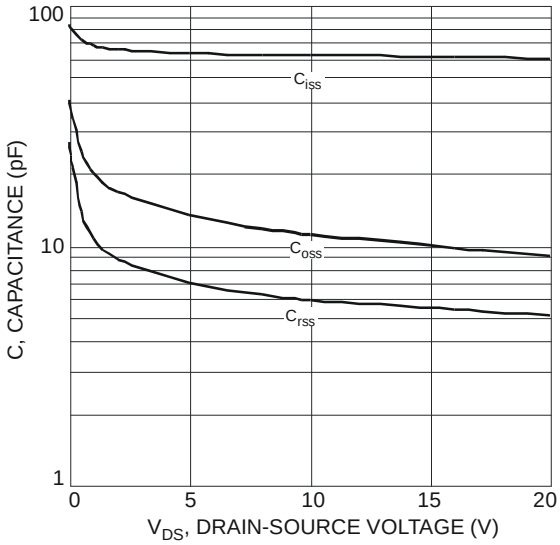


Fig. 9 Typical Total Capacitance

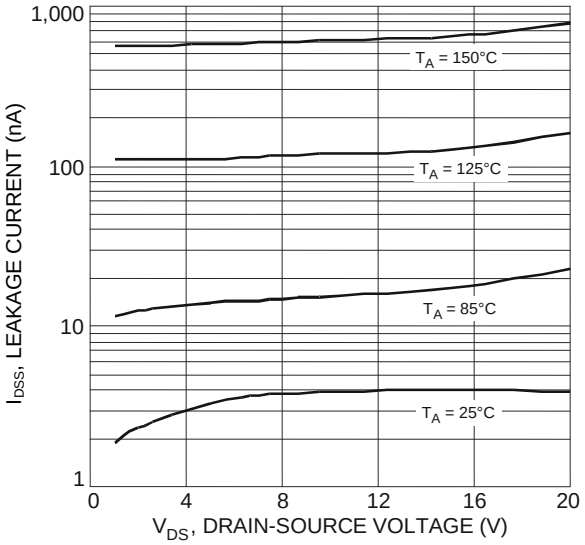


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

P-CHANNEL – Q2

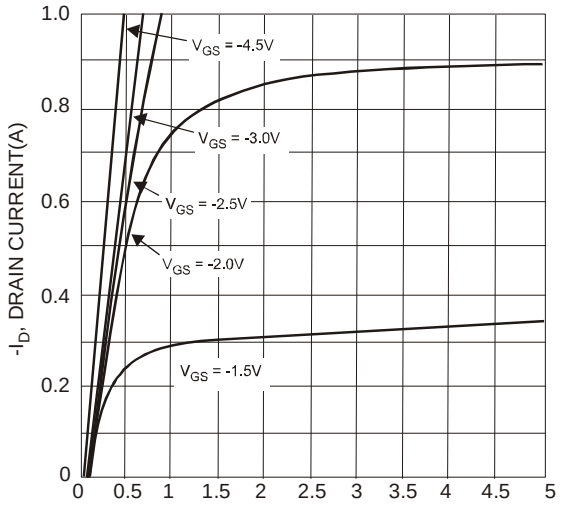


Fig.11 Typical Output Characteristics

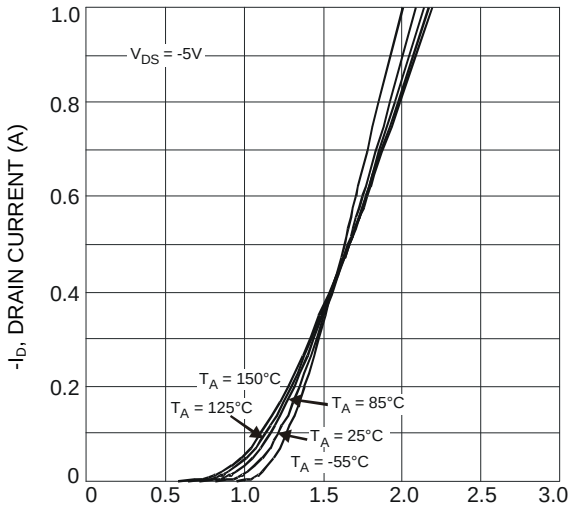


Fig. 12 Typical Transfer Characteristic

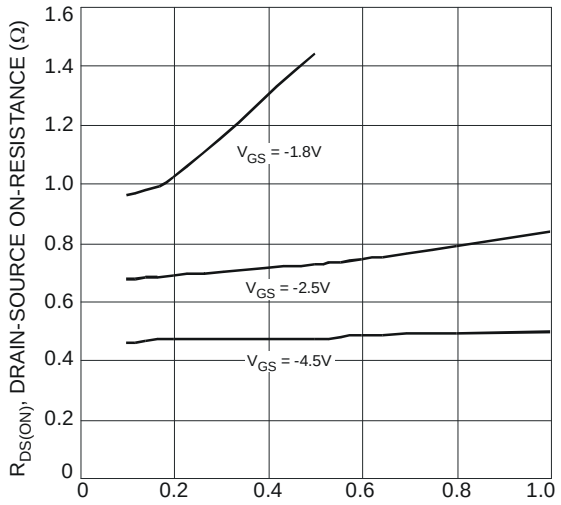


Fig. 13 Typical On-Resistance
vs. Drain Current and Gate Voltage

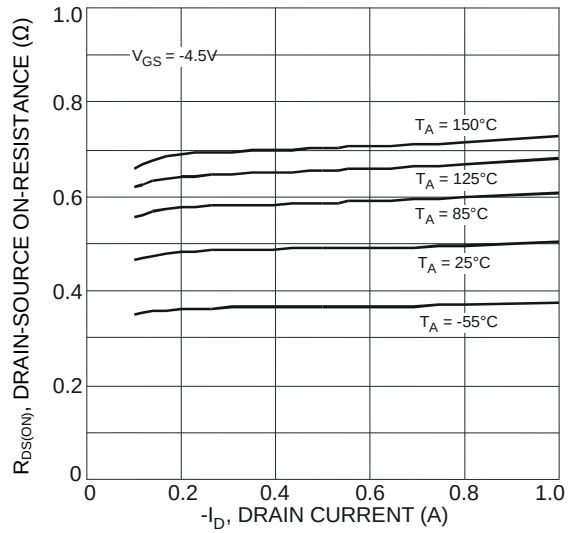


Fig. 14 Typical On-Resistance
vs. Drain Current and Temperature

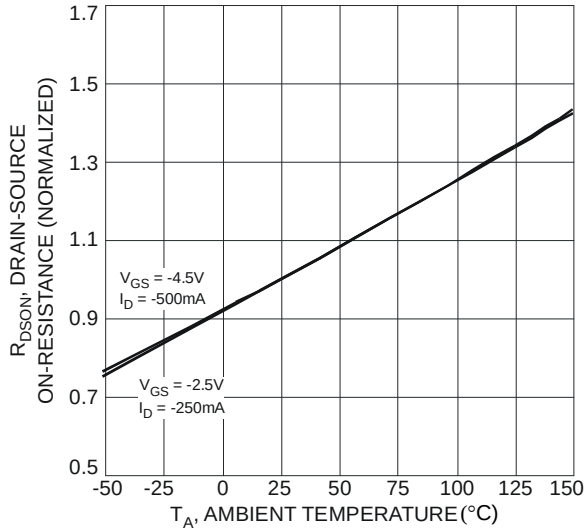


Fig. 15 On-Resistance Variation with Temperature

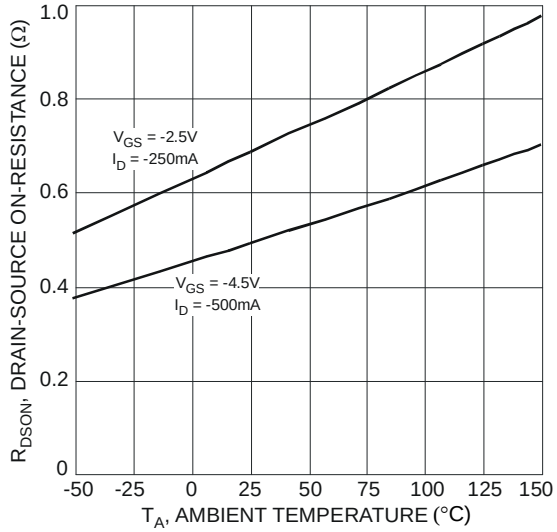


Fig. 16 On-Resistance Variation with Temperature

P-CHANNEL – Q2 (Cont.)

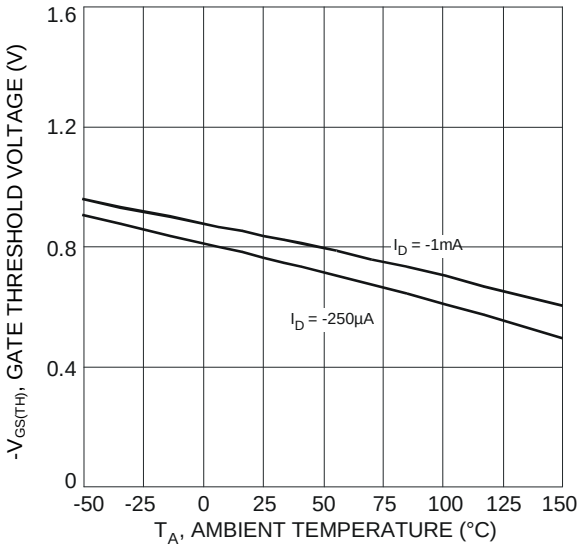


Fig. 17 Gate Threshold Variation vs. Ambient Temperature

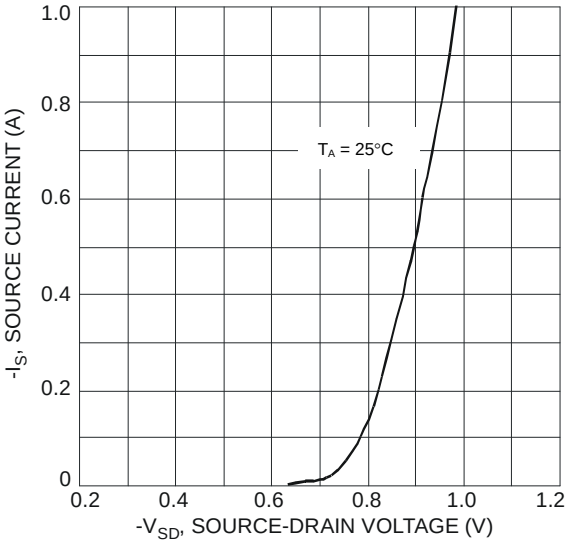


Fig. 18 Diode Forward Voltage vs. Current

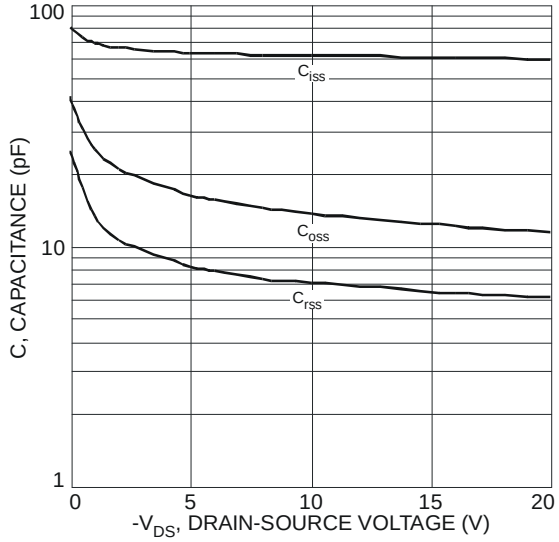


Fig. 19 Typical Total Capacitance

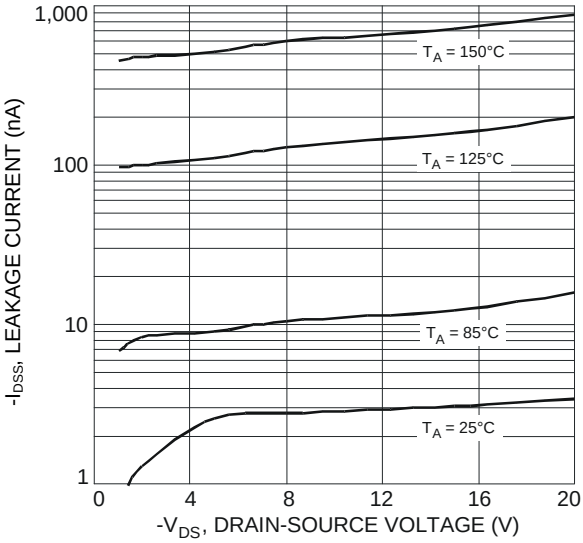
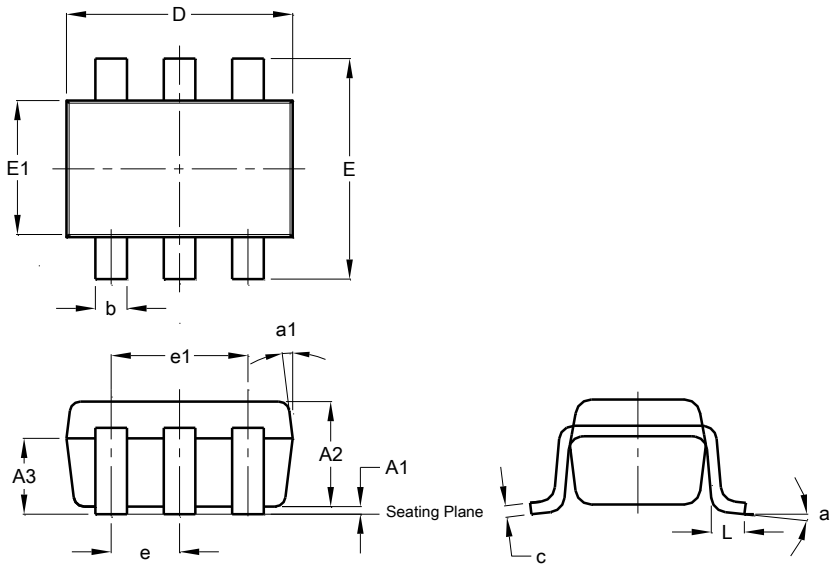


Fig. 20 Typical Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26

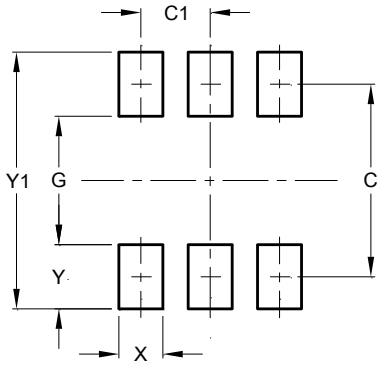


SOT26			
Dim	**Min**	**Max**	**Typ**
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

www.diodes.com